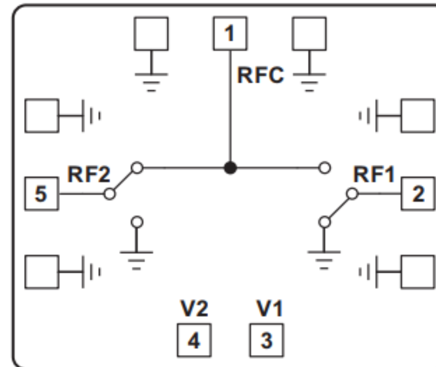
Features

- Isolation: >30dB @ 8GHz
- Insertion Loss: 0.75dB @ 8GHz
- Reflective design
- Die Size: 0.75x 0.7x 0.1 mm

Functional Block Diagram



Typical Applications

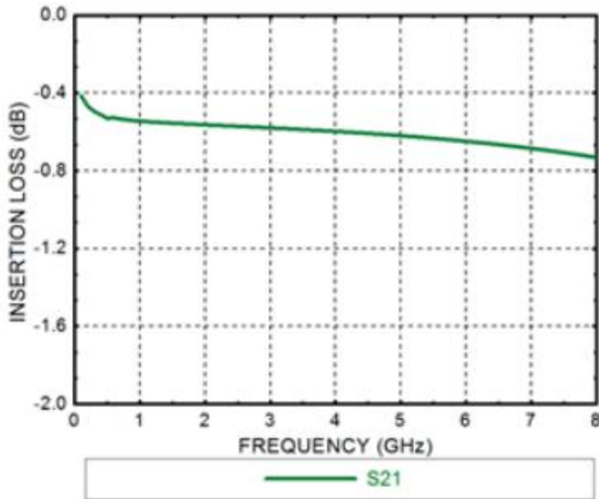
- TTL compatible driver included
- Fast Switching Speed
- Low Insertion Loss and High Isolation
- Customization available upon request

Electrical Specifications

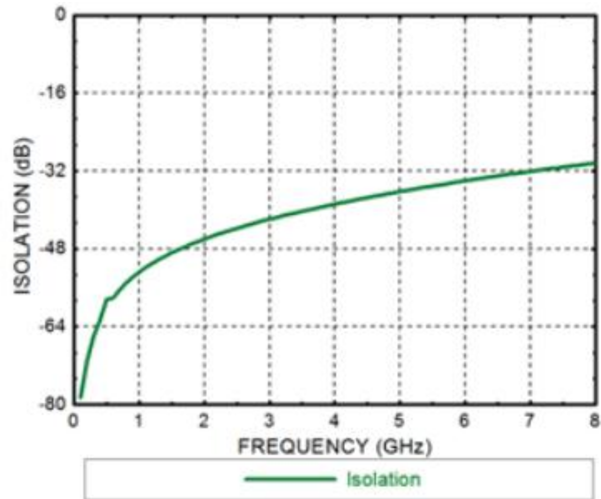
TA = +25°C, Vctl = 0/-5V

Parameters	Min.	Typ.	Max.	Units
Frequency	DC - 8			GHz
Insertion Loss		0.65		dB
Isolation		35		dB
Return Loss (ON State)		25		dB
Input 1dB Compression (P1dB)		25		dBm
Switching Speed		15		ns

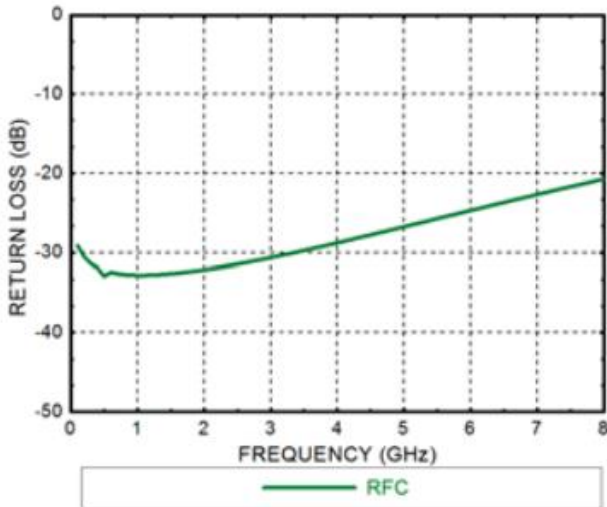
Insertion Loss



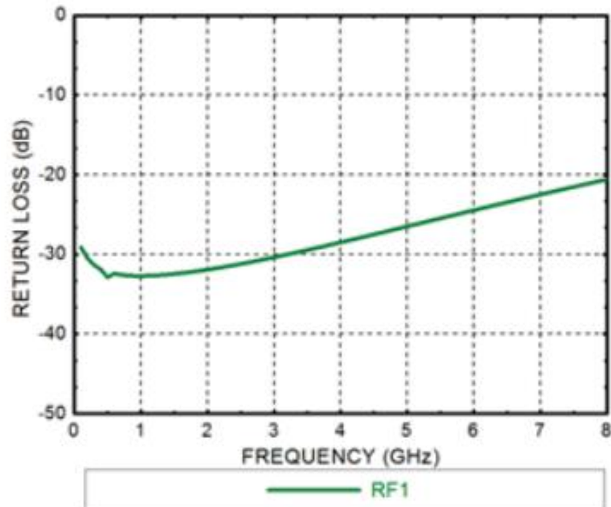
Isolation



RFC Return Loss(ON State)

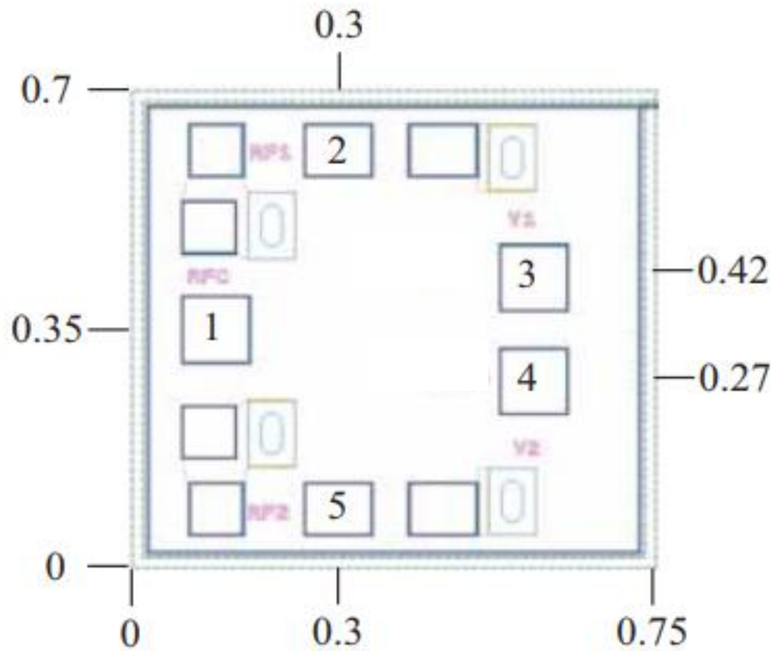


RF1 Return Loss(ON State)



Outline Drawing:

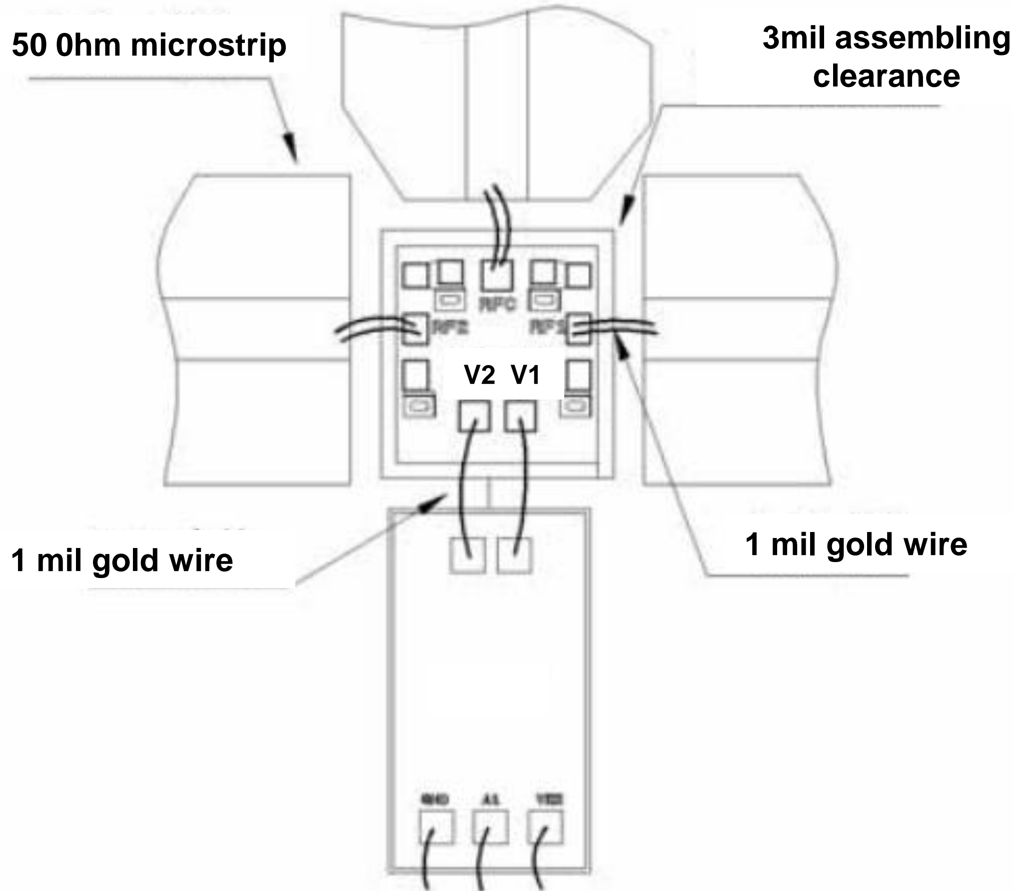
All Dimensions in mm



Pad Description

PAD	Function	Description
1	RFC	The pad is DC coupled to 50 ohms . If the RF level is not 0V, then the blocking capacitor is required externally.
2, 5	RF1，RF2	The pad is DC coupled to 50 ohms . If the RF level is not 0V, then the blocking capacitor is required externally.
3, 4	V1，V2	When V1=-5V,V2=0V, the RF1 is “ON” state；RF2 is “OFF” state When V1=0V, V2=-5V, the RF1 is “OFF” state；RF2 is “ON” state.
Die Bottom	GND	Die bottom must be connected to RF/DC ground.

Assembly Drawing



Notes:
1. Die thickness: 100um
2. Typical bond pad is 100*100 μm^2
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die (GND)
6. No connection required for unlabeled bond pads

Maximum Ratings:
1. RF input power: +27dBm
2. Storage temperature: -65℃ to +175℃
3. Operating temperature: -55℃ to +85℃